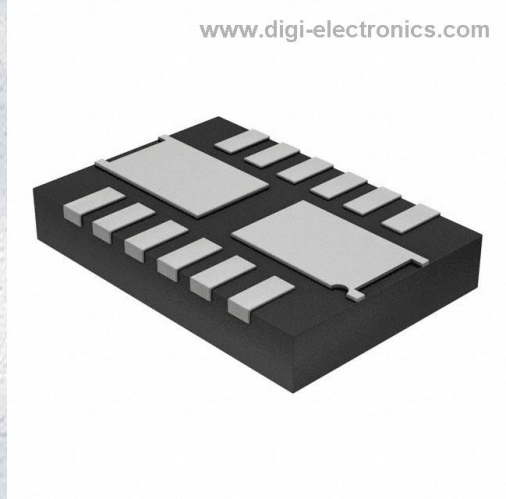
FDMD82100L Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	FDMD82100L-DG
Manufacturer	onsemi
Manufacturer Product Number	FDMD82100L
Description	MOSFET 2N-CH 100V 7A 12POWER
Detailed Description	Mosfet Array 100V 7A 1W Surface Mount 12-Power3 .3x5

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FDMD82100L	onsemi
Series:	Product Status:
PowerTrench®	Obsolete
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
Logic Level Gate	100V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
7A	19.5mOhm @ 7A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250µA	24nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
1585pF @ 50V	1W
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
12-PowerWDFN	12-Power3.3x5
Base Product Number:	
FDMD82	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

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ON Semiconductor®

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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

June 2014

FDMD82100L

Dual N-Channel PowerTrench® MOSFET

100 V, 24 A, 19.5 mΩ

Features

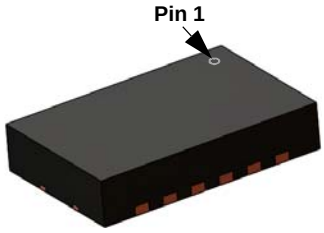
- Max $r_{DS(on)}$ = 19.5 mΩ at V_{GS} = 10 V, I_D = 7 A
- Max $r_{DS(on)}$ = 30 mΩ at V_{GS} = 4.5 V, I_D = 5.7 A
- Ideal for flexible layout in primary side of bridge topology
- Termination is Lead-free and RoHS Compliant
- 100% UIL tested
- Kelvin High Side MOSFET drive pin-out capability

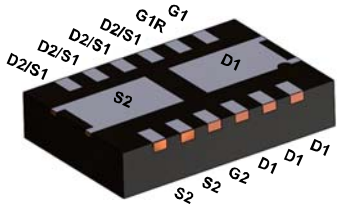
General Description

This device includes two 100V N-Channel MOSFETs in a dual Power (3.3 mm X 5 mm) package. HS source and LS Drain internally connected for half/full bridge, low source inductance package, low $r_{DS(on)}$/Qg FOM silicon.

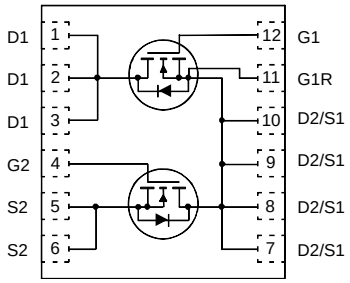
Applications

- Synchronous Buck : Primary Switch of Half / Full bridge converter for telecom
- Motor Bridge : Primary Switch of Half / Full bridge converter for BLDC motor
- MV POL : 48V Synchronous Buck Switch





Power 3.3 x 5



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			100	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous	T_C = 25 °C		24	A
	-Continuous	T_A = 25 °C	(Note 1a)	7	
	-Pulsed	T_A = 25 °C	(Note 4)	80	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	150	mJ
P_D	Power Dissipation	T_C = 25 °C		38	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.1	
	Power Dissipation	T_A = 25 °C	(Note 1b)	1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	60	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	130	

Package Marking and Ordering Information

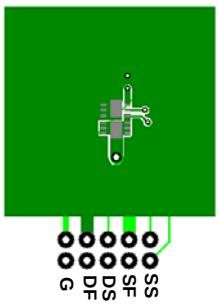
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
82100L	FDMD82100L	Power 3.3 x 5	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

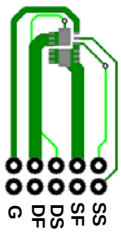
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		70		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 7 A		13.5	19.5	mΩ
		V_{GS} = 4.5 V, I_D = 5.7 A		17.9	30	
		V_{GS} = 10 V, I_D = 7 A, T_J = 125 °C		25	36	
g_{FS}	Forward Transconductance	V_{DD} = 5 V, I_D = 7 A		29		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V f = 1 MHz		1130	1585	pF
C_{oss}	Output Capacitance			173	245	pF
C_{rss}	Reverse Transfer Capacitance			8.1	15	pF
R_g	Gate Resistance		0.1	1.8	3.6	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 7 A V_{GS} = 10 V, R_{GEN} = 6 Ω		7.9	16	ns
t_r	Rise Time			2.8	10	ns
$t_{d(off)}$	Turn-Off Delay Time			21	34	ns
t_f	Fall Time			2.9	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 50 V, I_D = 7 A		17	24	nC
	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 50 V, I_D = 7 A		8	12	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 50 V, I_D = 7 A		3		nC
Q_{gd}	Gate to Drain “Miller” Charge			2.3		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 7 A (Note 2)		0.8	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 7 A, di/dt = 100 A/μs		42	67	ns
Q_{rr}	Reverse Recovery Charge			39	62	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 60 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 130 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.
3. E_{AS} of 150 mJ is based on starting T_J = 25 °C, L = 3 mH, I_{AS} = 10 A, V_{DD} = 90 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 31 A.
4. Pulse Id refers to Figure.11 Forward Bias Safe Operation Area.

Typical Characteristics (N-Channel) T_J = 25 °C unless otherwise noted

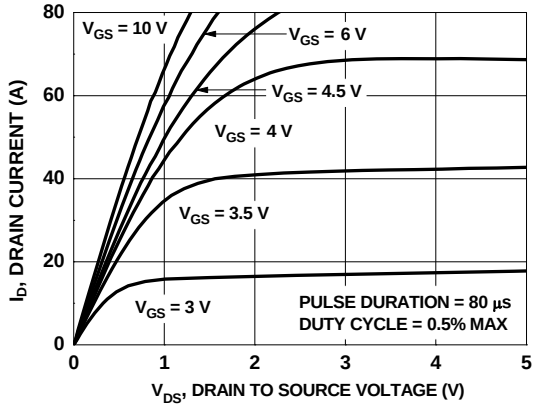


Figure 1. On Region Characteristics

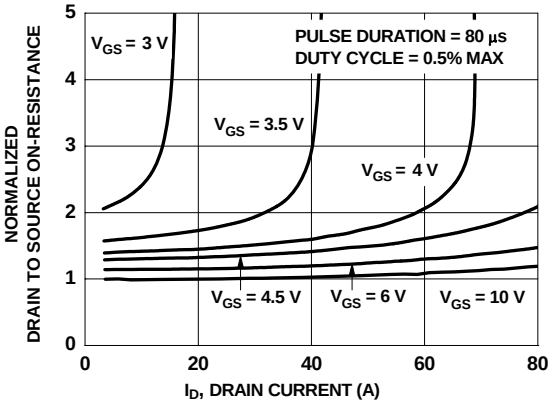


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

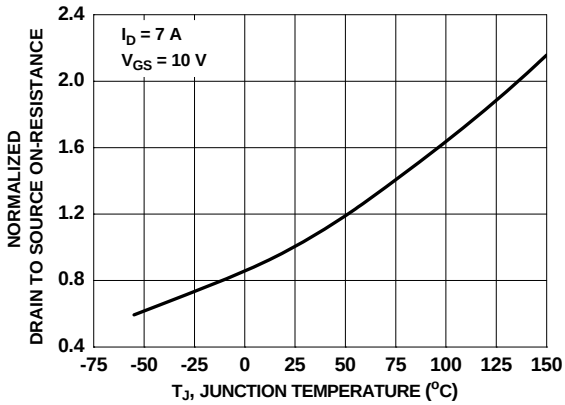


Figure 3. Normalized On Resistance vs Junction Temperature

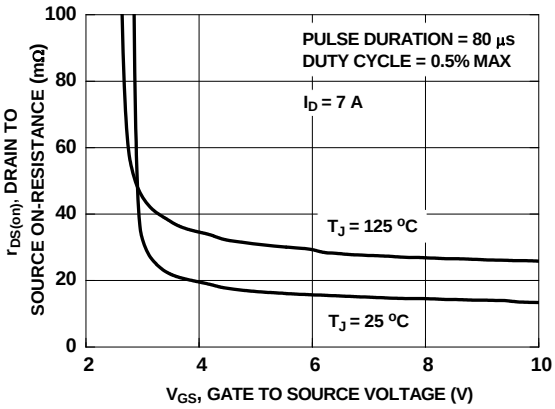


Figure 4. On-Resistance vs Gate to Source Voltage

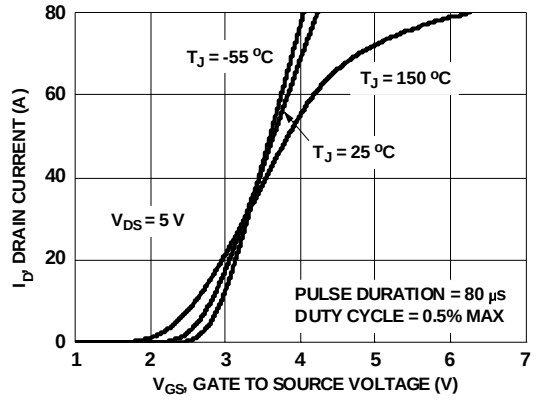


Figure 5. Transfer Characteristics

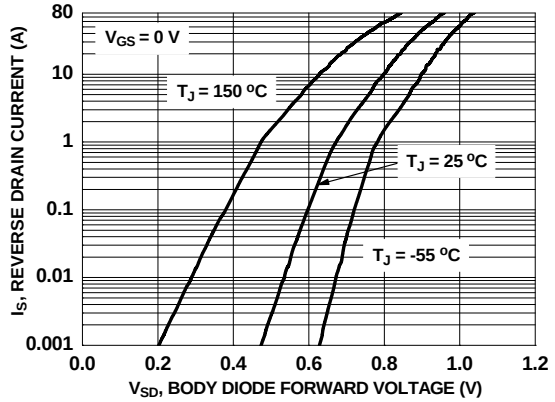


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (N-Channel) T_J = 25 °C unless otherwise noted

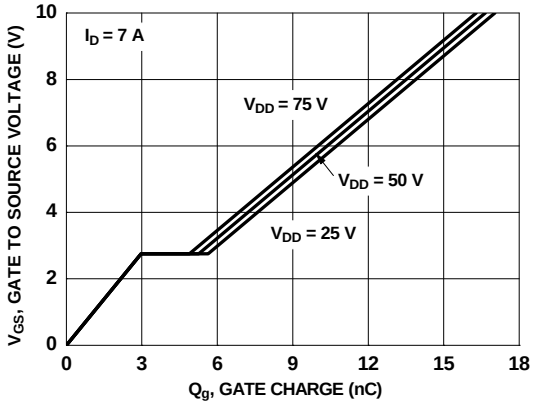


Figure 7. Gate Charge Characteristics

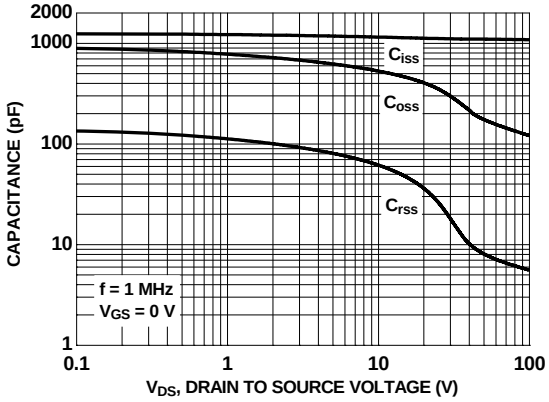


Figure 8. Capacitance vs Drain to Source Voltage

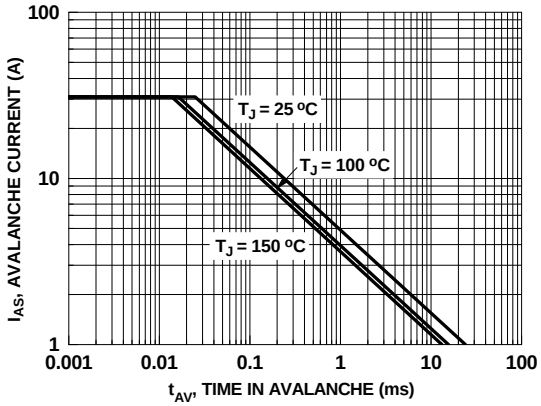


Figure 9. Unclamped Inductive Switching Capability

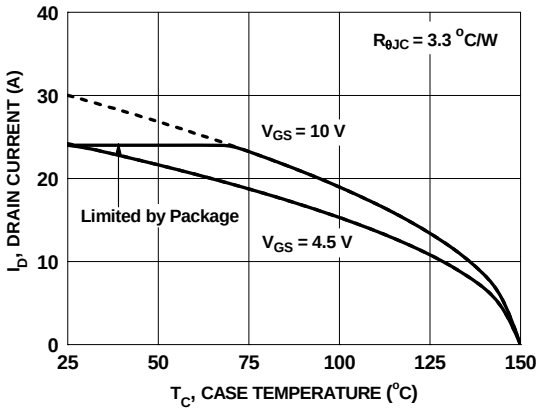


Figure 10. Maximum Continuous Drain Current vs Case Temperature

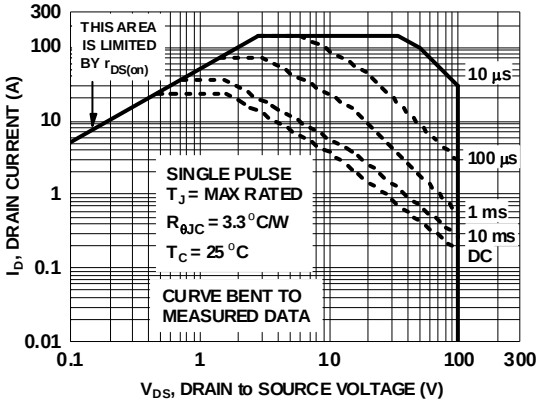


Figure 11. Forward Bias Safe Operating Area

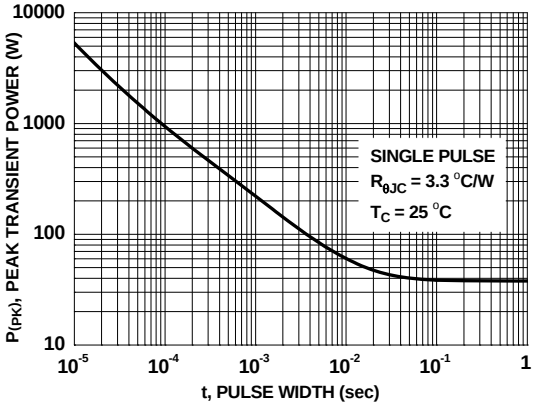


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics (N-Channel) T_J = 25 °C unless otherwise noted

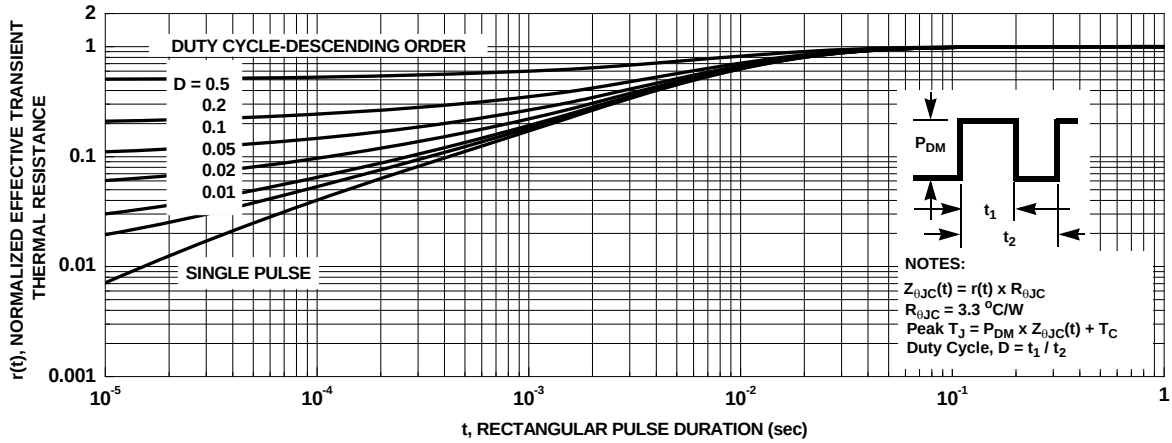
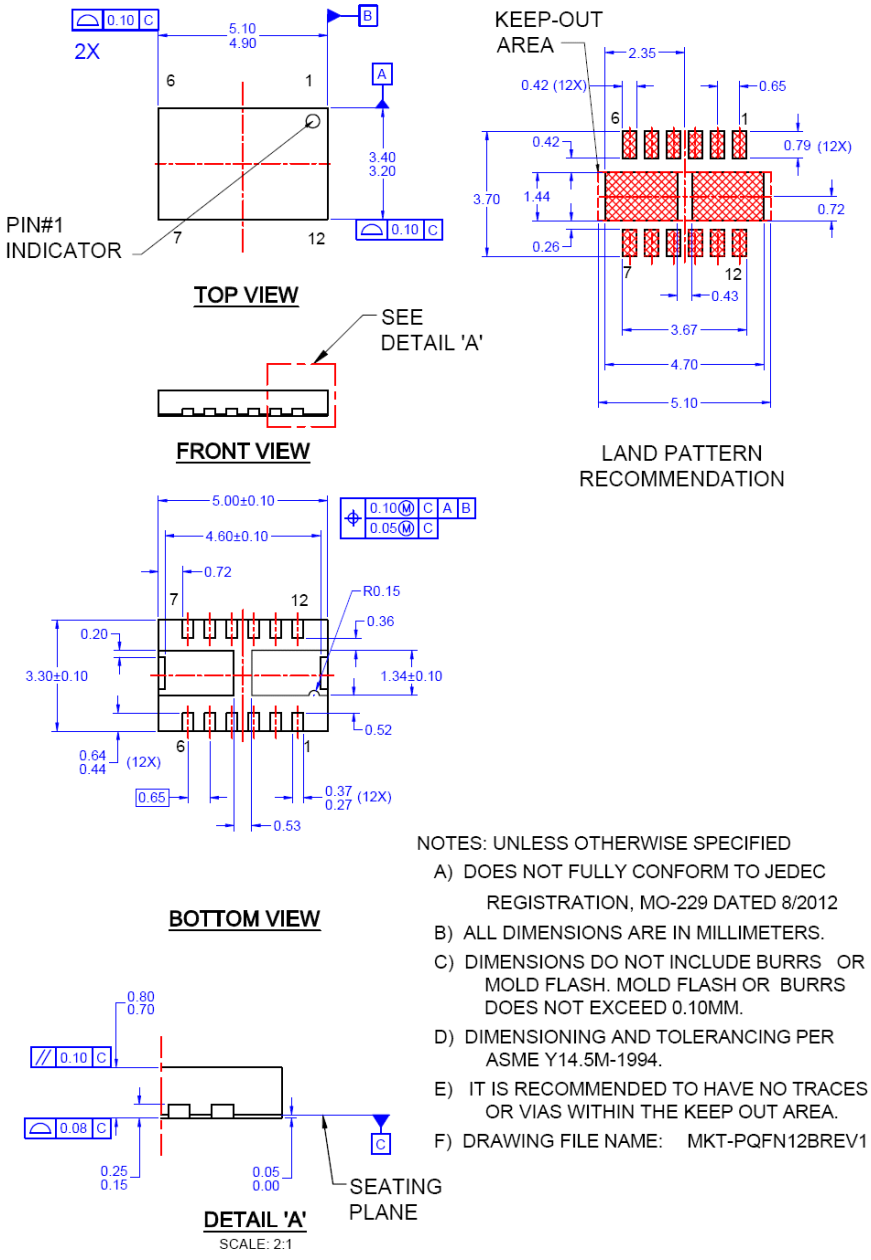


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout



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B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.

D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

E) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

F) DRAWING FILE NAME: MKT-PQFN12BREV1

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I68

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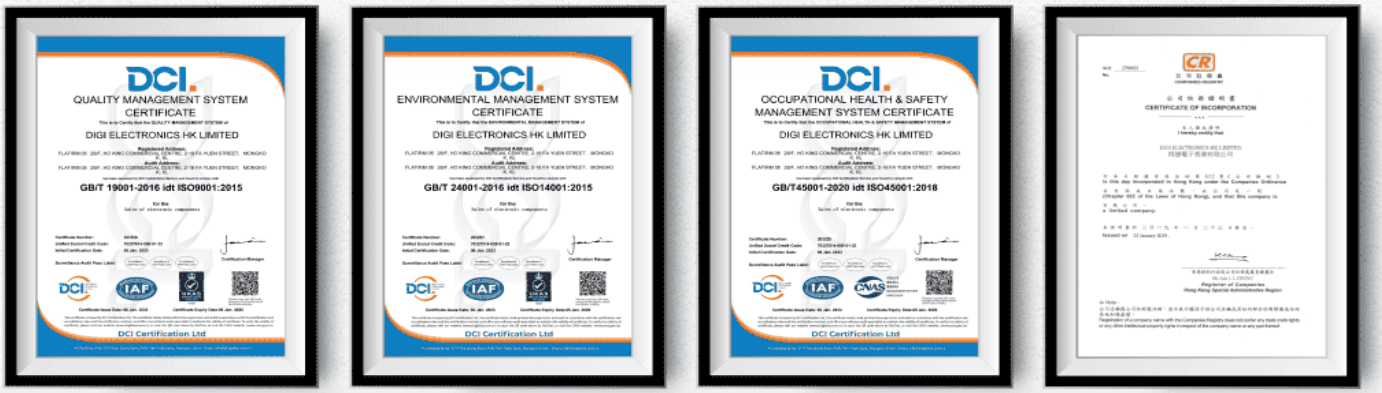

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